

Effect of Doping-induced Disorder on Transition Temperature in High T_c Cuprates

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We study the effect of disorder induced by doping on the transition temperature in high T_c cuprates. Since the impurity lies between the CuO_2 planes, the momentum transfer is restricted by small angle with a range of order of $1/(dk_F)$, where k_F is the Fermi momentum and d is the distance between the plane and the impurity. We find that the leading correction on the transition temperature in this case is in cubic order of $1/(dk_F)$, while the single particle scattering rate is linearly proportional to $1/(dk_F)$. Therefore, we conclude that the disorder induced by doping has rather small effect on T_c , while it could give large single particle scattering rate. We find that the reduction of T_c is about 3 – 10%, using the single particle scattering rate (150 – 450K) observed in the recent angle-resolved- photoemission-spectroscopy data on optimally doped Bi2212. The consequences of the small angle scattering in other physical quantities such as transport are also discussed.

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A recent angle-resolved-photoemission-spectroscopy (ARPES) experiment on Bi2212 shows temperature independent single particle scattering rate of about 150 – 450K. [1] The scattering rate extracted to zero temperature shown in the ARPES in the normal state has been one of the puzzling issues in high T_c cuprates. Assuming that impurity is responsible for such a large elastic scattering rate in ARPES data, one should be able to answer the following questions: 1. Why there is no substantial pair-breaking effect due to impurity. 2. Why the transport scattering rate estimated from optical conductivity [2] or residual resistivity shows anomalously small effect of impurity. P. W. Anderson argued in a recent paper that this should be a clear evidence of the existence of “quantum protectorate” in high T_c cuprates because, in conventional d-wave superconductors, these impurities should act as strong pair-breakers and lower T_c down to zero temperature. [3] Indeed, the impurity effect in the unitary limit on the d-wave superconductors was studied in [4] and it was shown that the critical scattering rate which reduces T_c down to zero temperature is $0.88T_c$.

In order to get further insights in this issue, let us recall some of the basic features of high T_c cuprates. One of the most important features of these materials is that the superconducting state occurs only away from half filling. It is clear that in any well-prepared cuprate sample there are always impurities coming from non-stoichiometry. Naively, then, one may conclude that the doping-induced impurities [5] should act as strong pair-breakers and reduce T_c substantially since the superconducting state has d-wave symmetry. However, in experiments, these impurities do not act as strong pair-breakers. Therefore, it is important to understand why they have small effect on T_c and also on the transport scattering rate, but large effect on the single particle scattering rate.

In this paper, we investigate how the doping-induced impurities act on the single particle scattering rate and the transition temperature T_c based on the conventional

d-wave BCS picture. We find that the reduction of T_c due to small angle scattering is rather small which shows the same effect as the transport scattering rate, but not the single particle scattering rate. Using the single particle scattering rate (150 – 450K) observed in ARPES we find that the reduction of the transition temperature is about 3 ~ 10% for $a/d = 1/4 \sim 1/2$ where a is the lattice constant and d is the distance between the impurity and CuO_2 plane. On the other hand, given the impurity scattering rate extracted from the ARPES data [1], T_c could be reduced down to zero temperature in the momentum-independent weak scattering (Born) limit.

There has been a clear evidence that, in optimally doped Bi2212, the imaginary part of the self energy along the nodal direction has a linear dependence on temperature, independent of energy for small binding energy, and a linear dependence on energy, independent of temperature for large binding energy. [6] The linear dependence of the imaginary part of self energy, $\text{Max}(T, \text{energy})$ is consistent with the prediction made based on a phenomenological characterization of the high T_c materials as the marginal Fermi liquid. [7] It has been also shown that within resolution limit, the temperature independent scattering rate is about 150K at the nodal direction and increases as one moves away from the nodal direction. The temperature independent offset was explained by taking into account the small angle scattering due to the static impurities in the sample which are naturally induced by the doping of Sr (LSCO) and O (YBCO, BSCCO). [8] Furthermore, the idea of the angular dependence of the scattering rate around the Fermi surface was proposed by considering the angular dependence of the local density of states. [8]

The above discussion suggests an investigation of the effect of small angle scattering on the transition temperature. Let us consider the effect of doping in high T_c cuprates. The major effect of doping is, of course, changing the concentration of the charge carriers. Un-

derstanding the motion of the holes induced by doping in the antiferromagnetic background has been a long standing issue that is certainly related to the mechanism of superconductivity in the cuprates, which we do not address in this paper. On the other hand, the doping (say, by Sr in LSCO) introduces impurities between the CuO_2 planes. Therefore, we can expect that the effect of this kind of disorder can be represented by a smooth elastic scattering potential. The following form of the potential scattering can faithfully represent the effect of disorder induced by doping.

$$u(\mathbf{r} - \mathbf{r}') = \frac{u_0}{r^2 + d^2}, \quad (1)$$

where $r = |\mathbf{r} - \mathbf{r}'|$ and u_0 is the amplitude of the scattering potential.

In order to represent the impurity scattering in the momentum space, we need to take a model Fermi surface. We consider the simplest circular Fermi surface with the origin located at $(0,0)$, where a is the lattice spacing. The Fermi momentum measured from $(0,0)$ depends on the doping concentration. For example, in the case of the optimally doped Bi2212, it is reasonable to take $k_F \sim \frac{4\pi}{5a}$. [1]

Taking a Fourier transform of the elastic potential, Eq. (1), with the model Fermi surface, we find that the scattering potential is represented by the modified Bessel function of the second kind, $K_0(d|\mathbf{k} - \mathbf{k}'|)$. Therefore, it is reasonable to assume that the scattering potential is finite only for a range of small angles and can be described as

$$u(\mathbf{k} - \mathbf{k}') = \begin{cases} u_0 & \text{for } \phi - \phi' < \theta_c \\ 0 & \text{otherwise} \end{cases}, \quad (2)$$

where $\theta_c = \frac{1}{dk_F}$ and ϕ is the angle measured from the k_x -axis. It is important to notice that the small momentum transfer (small angle scattering) is dominant in the scattering process. The change of the angle due to the scattering is restricted by $\frac{1}{dk_F}$. Therefore, our analysis on the effect of the impurity on T_c has to be distinguished from momentum-independent scattering, either Born (weak) or unitary (strong) limit. It can also be shown that the momentum transfer due to impurity can be even smaller if the scattering potential is short-ranged than the interaction form of Eq. (1).

Let us consider the effect of the impurity potential, Eq. (2). Since the effect of the impurity manifests itself through the self energy, let us first compute the self energy renormalized by the impurity scattering. Assuming that the superconducting state is described by the d-wave BCS superconductivity, we obtain the self energy using the standard method described in [9]. The self energy is written as

$$\Sigma(\mathbf{k}, \tilde{\omega}) = -\frac{n_i u_0^2}{2} \int_{\phi}^{\phi + \theta_c} d\phi' N(\phi') \frac{i\tilde{\omega} + \tilde{\Delta}_0 \cos(2\phi') \rho_1}{\sqrt{\tilde{\omega}^2 + \tilde{\Delta}_0^2 \cos^2(2\phi')}}, \quad (3)$$

where $N(\phi)$ is the local density of states given by $N(\phi) = \frac{m}{(2\pi)}$. Here n_i is the impurity concentration and ρ_i are the Pauli matrices in the particle-hole space. The dispersion of the quasiparticle in the normal state behaves as $\xi_{\mathbf{k}} = v_F p$, where v_F is the Fermi velocity and $p = |\mathbf{k} - \mathbf{k}_F|$ to obtain Eq. (3). The scattering rate in the normal state with our model Fermi surface can be easily obtained by taking $\tilde{\Delta}_0 = 0$ and it is given by

$$\frac{1}{\tau}(\phi) = \frac{n_i u_0^2}{2} N(\phi) \theta_c. \quad (4)$$

As one can see, the scattering rate is proportional to the local density of states $N(\phi)$, multiplied by θ_c . Therefore, the scattering rate is proportional to the inverse of the Fermi velocity, $1/v_F$. Since our model Fermi surface is circular, the Fermi velocity is independent of the angle ϕ and so is the single particle scattering rate.

The angle dependence of the scattering rate observed by ARPES [1] in the normal state ($\tilde{\Delta}_0 = 0$) should originate from the angle dependence of local density of states through the Fermi velocity on the actual Fermi surface. This can be seen through the simple analysis as follows. Considering the actual Fermi surface shown in [1], we find that the Fermi momentum depends on the angle ϕ around the Fermi surface. The doping-induced impurity potential, Eq. (1) will lead to the same result that the scattering is finite only for small range of the angle, θ_c , which is now restricted by $1/[d\sqrt{k_F^2 + (dk_F/d\phi)^2}]$. On the other hand, the local density of states will be given by $N(\phi) = m^* \sqrt{k_F^2 + (dk_F/d\phi)^2} / (2\pi k_F)$, where m^* is the effective mass. Using the fact that the scattering is finite only for small range of the angle around the Fermi surface, we can expand the integrand of Eq. (3) up to linear order in θ_c in the normal state ($\tilde{\Delta} = 0$). Then the single particle scattering rate is given by

$$\frac{1}{\tau}(\phi) = \frac{n_i u_0^2}{2d} \frac{1}{v_F(\phi)} \quad (5)$$

Therefore, the single particle scattering rate depends on the angle around the Fermi surface through the angular dependence of the Fermi velocity at each point on the Fermi surface. Although, the angular dependence of the single particle scattering rate itself is an interesting issue and was used to explain the line shape of the ARPES in [7], we will show below that our analysis of the effect of small angle scattering on transition temperature, qualitatively, does not depend on whether the scattering rate depends on angle or not. We will keep the angle dependence of the local density of states to make our analysis more general. But we show below that the reduction of T_c within our model Fermi surface by taking $N(\phi) = \text{constant}$ is comparable with the result obtained with the angle dependent scattering rate.

Let us proceed to determine the reduction of the transition temperature due to impurity using the method described in [9]. We first consider the transition temperature in the absence of impurity, which is obtained by taking $\Delta_0 = \tilde{\Delta}_0 \rightarrow 0$ in the gap equation,

$$\Delta_0 = 8V_0T \sum_{n=1}^{\infty} \int_0^{\pi/2} d\phi N(\phi) \frac{\tilde{\Delta}_0 \cos^2(2\phi)}{\sqrt{\tilde{\omega}_n^2 + \tilde{\Delta}_0^2 \cos^2(2\phi)}}. \quad (6)$$

One can see that the transition temperature T_{c0} in the absence of impurity is given by

$$T_{c0} = \frac{2\gamma\omega_c}{\pi} \exp(-1/[8V_0 \int_0^{\pi/2} \frac{d\phi}{2\pi} N(\phi) \cos^2(2\phi)]), \quad (7)$$

where ω_c is the cut-off frequency determined by the effective attractive interaction strength and $\gamma = 1.768$.

In the presence of impurity, one needs to compute the ratio $\frac{\tilde{\Delta}_0}{\omega_c}$, which can be obtained by using Eq. (3) and the Dyson equation. One can show that the gap equation can be written as

$$1 = 4V_0T_c \sum_{n=1}^{\infty} \int_0^{\pi/2} d\phi \left[\frac{N(\phi) \cos^2(2\phi)}{\omega_n} - n_i u_0^2 \frac{N(\phi)^2 \cos^2(2\phi) + N(\phi) \frac{dN(\phi)}{d\phi} \cos(2\phi) \sin(2\phi)}{\omega_n^2} \theta_c^3 \right], \quad (8)$$

where $\omega_n = \pi T(2n - 1)$. It is very important to notice that the leading order correction is of the order of θ_c^3 . The correction of the linear order in θ_c cancels out in analogy with Anderson theorem in the case of s-wave superconductor with non-magnetic impurity. There is no quadratic order in θ_c because of the symmetry of the order parameter, $\cos(2\phi)$. Thus, the transition temperature in the presence of doping-induced impurity is determined by

$$T_c = T_{c0} - \frac{\pi n_i u_0^2}{4} \left(\frac{A(k_F)}{B(k_F)} \right) \theta_c^3, \quad (9)$$

where

$$A(k_F) = \int_0^{\pi/2} d\phi \left[N(\phi)^2 \cos^2(2\phi) + N(\phi) \frac{dN(\phi)}{d\phi} \cos(2\phi) \sin(2\phi) \right],$$

$$B(k_F) = \int_0^{\pi/2} d\phi N(\phi) \cos^2(2\phi). \quad (10)$$

We have to emphasize the fact that the leading order correction in cubic order of θ_c does *not* depend on the shape of the Fermi surface. This is a very robust feature due to symmetry of the order parameter. However, the coefficients A and B depend on the shape of the actual Fermi surface through the local density of states. To evaluate the change of T_c , we have to compute A and B in Eq.

(10). The expressions for A and B were obtained by expanding the integrand of the self energy in Eq. (3), to quadratic order in θ_c . This is valid because scattering is finite only for a small range of the angle ϕ .

Let us first estimate the reduction of T_c using our model circular Fermi surface. The scattering rate, $\theta_c (= 1/(dk_F))$, and local density of states are independent of angle. In this case, the change of T_c is equal to $(\pi/2)(1/\tau)\theta_c^2$. Taking $1/\tau = 200K$ which would lower T_c down to zero temperature in the momentum-independent Born limit, the doping-induced disorder lowers T_c by about 6% only for $a/d = 1/3$.

To extract more practical value of the reduction of T_c , let us use the scattering rate observed by ARPES data and assume that it is proportional to the local density of state, $N(\phi)$. Also θ_c is independent of angle. The scattering rate observed by ARPES behaves as

$$\frac{1}{\tau(\phi)} = \Gamma_1 \cos^2(2\phi) + \Gamma_0, \quad (11)$$

where Γ_0 can be obtained from ARPES data. The minimum scattering rate at the node is about $150K$ and the maximum is about $450K$, if we extract zero-temperature offset from Ref. [1]. Therefore, we choose $\Gamma_0 = 150K$ and $\Gamma_1 = 300K$. Taking $\theta_c \sim 1/(dk_F) \sim (5a)/(4\pi d)$, we obtain

$$\frac{T_{c0} - T_c}{T_c} = 0.03 \sim 0.1 \quad (12)$$

where we use $T_c = 91K$ and $\frac{d}{a} = 2 \sim 4$. As we shown here, the effect of small angle scattering due to doping-induced impurity on T_c is rather small for both cases.

It was discussed in [8] that the transport scattering rate would be in cubic order of θ_c . Our result implies that the impurities have small effect on both T_c and the transport scattering rate in an exactly similar manner, while it has rather large effect on the single particle scattering rate. Therefore, invoking the basic features of the cuprates, we explain that the large scattering rate shown in ARPES does not contradict with the clean behavior in the transport and the small effect on the transition temperature.

Let us discuss the difference between the impurity in the CuO_2 plane (such as Zn or Ni) and the impurity induced by doping. The impurity induced by doping resides between the layers while Zn or Ni impurities go into the CuO_2 planes by replacing Cu sites. It has been well established that small concentration of transition metal ions which replace Cu sites can reduce the transition temperature substantially and shows the insulating behavior in in-plane resistivity. [10,11] It is clear that the doping-induced disorder should have stronger effect on out-of-plane resistivity, because the scattering is not restricted by small range of angle, and could lead insulating behavior in out-of-plane resistivity. [12] However, the nature of pseudogap behavior in the CuO_2 plane observed in many different experiments [13] and the hopping matrix

elements between the CuO_2 layers through the apical O [14,15] should be also considered for a complete analysis of the transport, which is beyond the scope of the present paper.

To summarize, we investigated the effect of impurity induced by doping on the transition temperature in high T_c cuprates. Since the impurity induced by doping resides between CuO_2 planes, small momentum transfer is dominant in the scattering process. This can be well described by the elastic scattering potential which is finite only for a small range of the angle, $\theta_c \sim 1/(dk_F)$. By computing the single particle Green function renormalized by the impurity scattering and solving the gap equation self consistently, we found that the leading correction on the transition temperature is in cubic order of θ_c . The effect of doping-induced disorder on T_c shows the same effect as the transport scattering rate discussed in [8]. Therefore, the reduction of T_c is related to the transport scattering rate, not the single particle scattering rate. Using the actual value of the scattering rate observed by ARPES [1], we estimated the change of the transition temperature. The reduction of the transition temperature for the optimally Bi2212 is about $3 \sim 10\%$, while momentum-independent weak scattering (nonmagnetic impurity in CuO_2 plane) could lower T_c down to zero temperature. Therefore, we conclude that the large elastic scattering shown in ARPES does not contradict with either no evidence of strong reduction of T_c or the small effect of impurity on the transport.

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